

## P-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
- 100	0.032 at $V_{GS} = - 10$ V	- 28	7.6 nC
	0.036 at $V_{GS} = - 4.5$ V	- 25	

### FEATURES

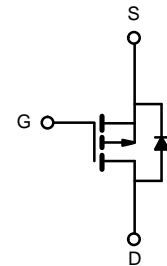
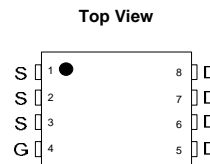
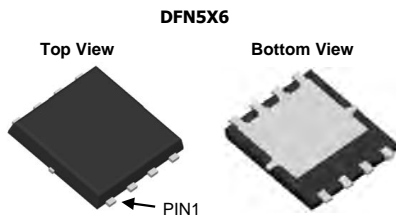
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % UIS Tested

### APPLICATIONS

- Load Switch



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	- 100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	- 28 <sup>a</sup>
		$T_C = 70$ °C	- 27
		$T_A = 25$ °C	22.2 <sup>b</sup>
		$T_A = 70$ °C	- 26.1 <sup>b</sup>
Pulsed Drain Current	$I_{DM}$	- 15	A
Avalanche Current Pulse	$I_{AS}$	- 4.5	
Single Pulse Avalanche Energy	$E_{AS}$	10.1	mJ
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25$ °C	6.9 <sup>a</sup>
		$T_A = 25$ °C	2.1 <sup>b</sup>
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	10.4 <sup>a</sup>
		$T_C = 70$ °C	6.6 <sup>a</sup>
		$T_A = 25$ °C	1.1 <sup>b</sup>
		$T_A = 70$ °C	2 <sup>b</sup>
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b</sup>	$R_{thJA}$	33	40	°C/W
Maximum Junction-to-Case				

Notes:

a. Based on  $T_C = 25$  °C.

b. Surface mounted on 1" x 1" FR4 board.

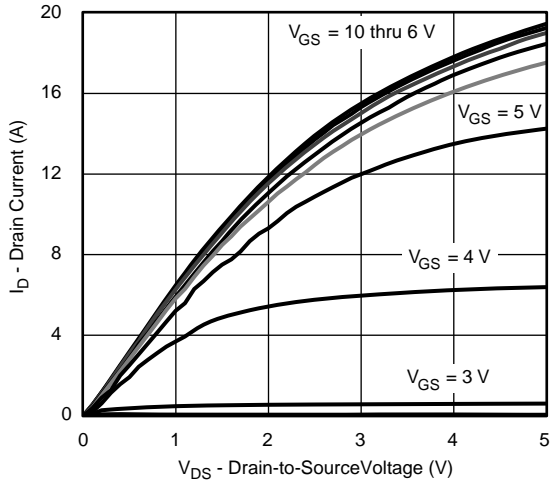
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-100			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		68		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-5.2		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1.8		-3	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-120			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -3\text{ A}$		0.032		$\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -2\text{ A}$		0.036		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -15\text{ V}, I_D = -5\text{ A}$	20			S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		3500		pF
Output Capacitance	$C_{oss}$			390		
Reverse Transfer Capacitance	$C_{rss}$			290		
Total Gate Charge	$Q_g$	$V_{DS} = -30\text{ V}, V_{GS} = -10\text{ V}, I_D = -5\text{ A}$		76	115	nC
				38	60	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$		16		
Gate-Drain Charge	$Q_{gd}$			19		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		5.2		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -2\text{ V}, R_L = 2\text{ }\Omega$ $I_D = -5\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		10	15	ns
Rise Time	$t_r$			7	15	
Turn-Off Delay Time	$t_{d(off)}$			70	110	
Fall Time	$t_f$			40	60	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			-6.9	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				-15	
Body Diode Voltage	$V_{SD}$	$I_S = -3\text{ A}$		-1	-1.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -5\text{ A}, di/dt = 10\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		45	68	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			59	120	nC
Reverse Recovery Fall Time	$t_a$			29		ns
Reverse Recovery Rise Time	$t_b$			16		

Notes:

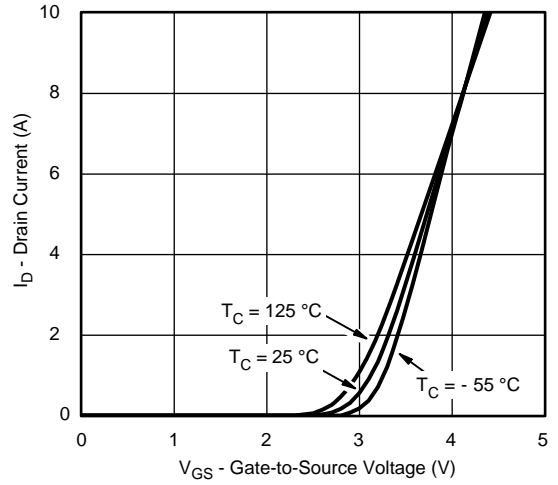
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



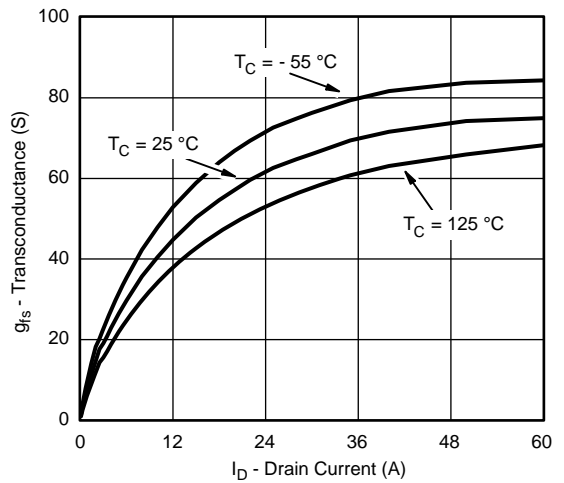
**Output Characteristics**



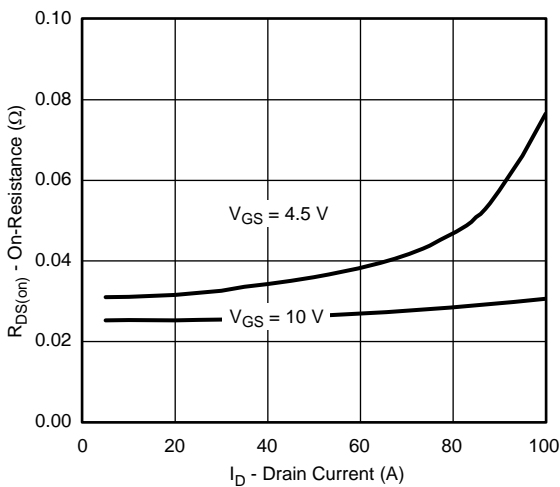
**Transfer Characteristics**



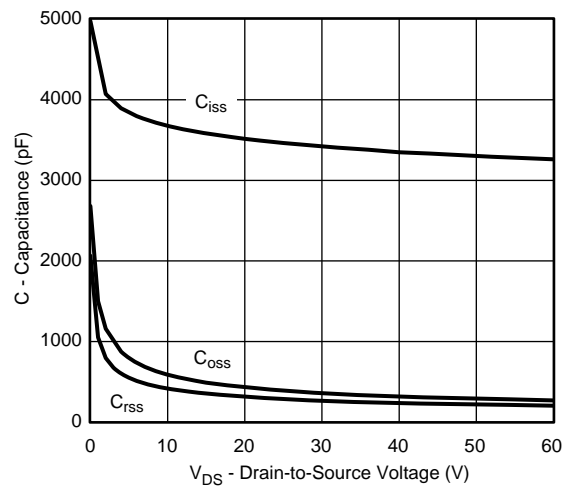
**Transfer Characteristics**



**Transconductance**

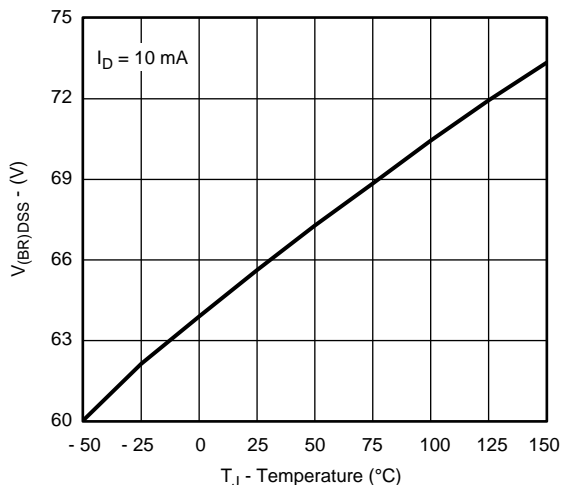
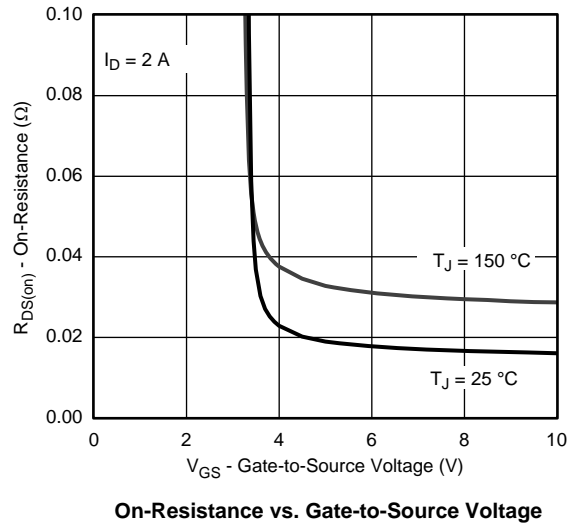
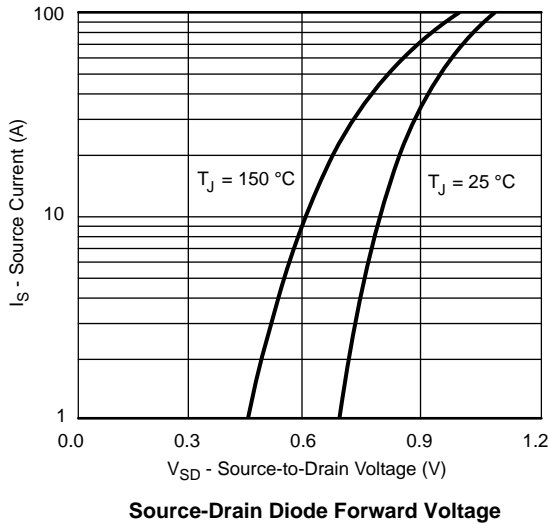
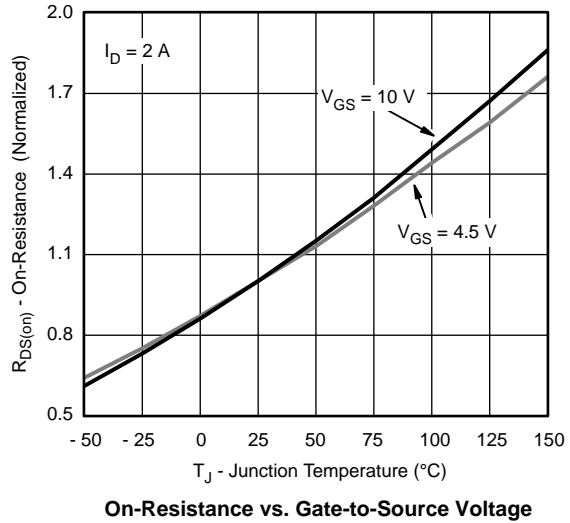
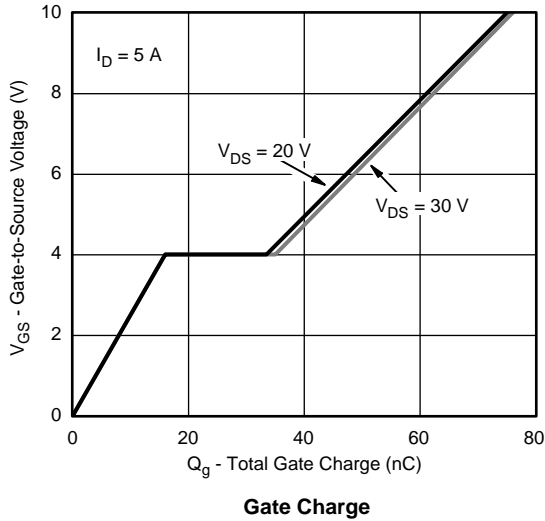


**On-Resistance vs. Drain Current**



**Capacitance**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Threshold Voltage**



**Max. Drain Current vs. Case Temperature**



**Power Derating, Junction-to-Case**

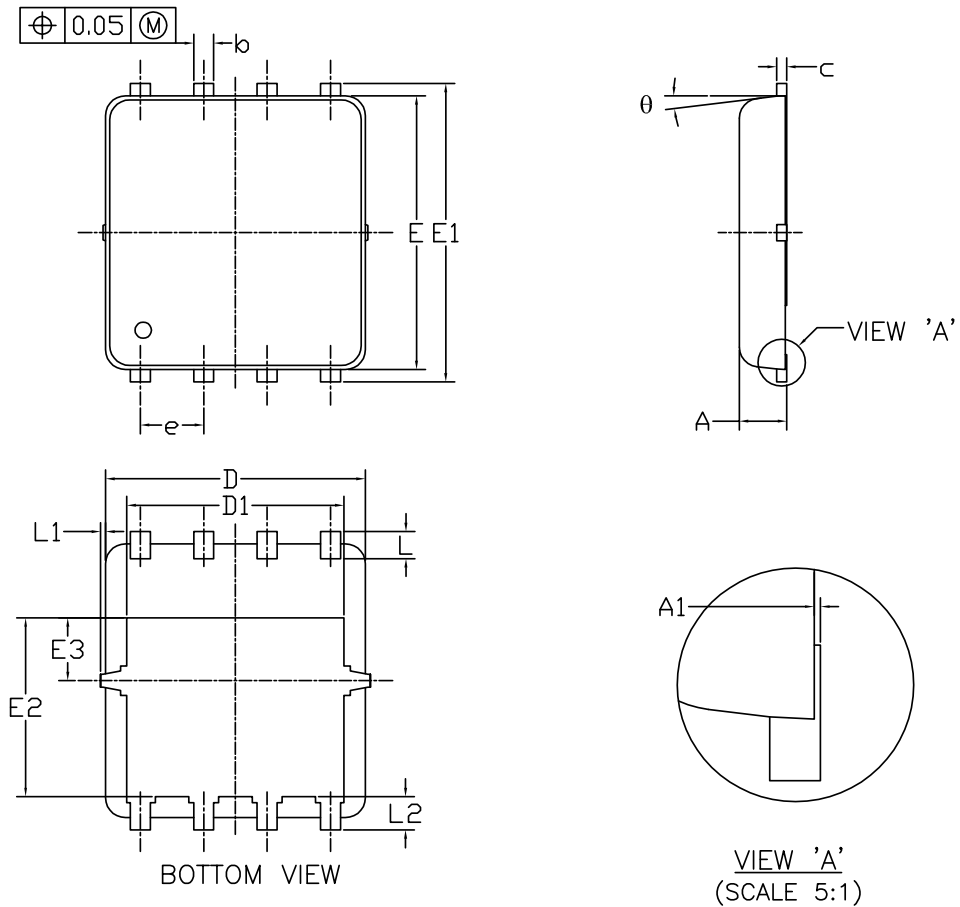


**Safe Operating Area, Junction-to-Case**



**Normalized Thermal Transient Impedance, Junction-to-Case**

DFN5x6\_8L\_EP1\_P PACKAGE OUTLIN



RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
$\theta$	0°	---	10°	0°	---	10°

NOTE

UNIT: mm

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.  
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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